

1. PRODUCT Schottky barrier Diode (Silicon Epitaxial Planar)
 2. TYPE **RB521SU-40**
 3. APPLICATION Small current rectification
 4. FEATURES Small mold type (EMD2_UT)
 High reliability
 Super low VF

5. ABSOLUTE MAXIMUM RATINGS (at Tc=25°C unless otherwise specified)

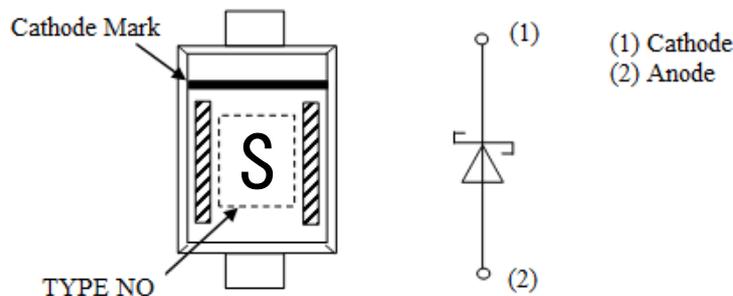
Item	Symbol	Condition	Rating	Unit
Repetitive Peak Reverse Voltage	VRM	Duty ≤ 0.5	45	V
Reverse Voltage	VR	Direct reverse voltage	40	V
Average Current	Io	Glass epoxy board mounted, 60Hz half sin wave, resistive load	200	mA
Non-repetitive Forward Surge Current	IFSM	60Hz half sin wave, one cycle, non-repetitive at Ta=25°C	1	A
Operating Junction temperature	Tj	-	150	°C
Storage temperature	Tstg	-	-55 ~ 150	°C

6. ELECTRICAL CHARACTERISTICS (at Tj=25°C unless otherwise specified)

Characteristic	Symbol	Test Condition	Specification			Unit
			Min.	Typ.	Max.	
Forward Voltage	VF1	IF=10mA	0.16	0.26	0.30	V
	VF2	IF=100mA	0.31	0.395	0.45	V
	VF3	IF=200mA	0.41	0.495	0.54	V
Reverse Current	IR1	VR=10V	-	3.5	20	μA
	IR2	VR=40V	-	13	90	μA

* Please pay attention to static electricity when handling.

7. MARKING



「S」 is the sign which shows RB521SU-40.
 There is dot on the package which tells production year,
 week and its product manufacture.

Attention in use
 Compared with PN junction diodes, Schottky Barrier Diode generally have higher IR (Reverse leakage current). So that the reverse loss of the diode will increase as temperature increase causing heat up and resulting further increase of IR.
 This phenomenon will be cause of overheat destruction of the diode.
 Therefore please give consideration to the reverse loss and around temperature when using this product.

DESIGN <i>K. Waki</i>	CHECK	APPROVAL <i>Y. Nagai</i>	DATE: 17.NOV.2020	SPECIFICATION No. : RB521SU-40-E
			REV. : C	ROHM Co.,Ltd.